

L Number	Hits	Search Text	DB	Time stamp
1	1	((esd or (electrostatic adj discharge)) adj protection) and (anti adj punch adj through adj structures)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:30
2	3	((esd or (electrostatic adj discharge)) adj protection) and (anti adj punch adj through)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:23
3	167	anti adj punch adj through	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:24
4	2	anti adj punch adj through adj structure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:24
5	14	((esd or (electrostatic adj discharge)) adj protection) and (internal adj mos)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 15:14
6	1	6008080.pn. and pocket	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 15:52
7	2	6100141.pn. and internal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 15:52
-	2	((esd or (electrostatic adj discharge)) adj protection) and (active adj region) and (breakdown adj enhanced adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 09:40
-	387	((esd or (electrostatic adj discharge)) adj protection) and (active adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 17:22
-	1	((esd or (electrostatic adj discharge)) adj protection) and (reduce adj breakdown adj voltage adj across adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 17:23
-	1	((esd or (electrostatic adj discharge)) adj protection) and (reduce adj breakdown adj voltage adj across adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 17:24
-	41	((esd or (electrostatic adj discharge)) adj protection) and (reduce adj breakdown adj voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 17:32
-	0	((esd or (electrostatic adj discharge)) adj protection) and (first adj gate adj oxide adj thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 17:36
-	70	((esd or (electrostatic adj discharge)) adj protection) and (thick adj gate adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 17:41

-	0	((esd or (electrostatic adj discharge)) adj protection) and (multiple adj gate adj oxide adj thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 17:42
-	0	((esd or (electrostatic adj discharge)) adj protection) and (multiple adj gate adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 17:42
-	13	((esd or (electrostatic adj discharge)) adj protection) and (different adj gate adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 08:43
-	1	5861345.pn. and (aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 08:44
-	0	5656337.pn. and (aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 08:44
-	6	((esd or (electrostatic adj discharge)) adj protection) and (pocket adj implantations)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:20